

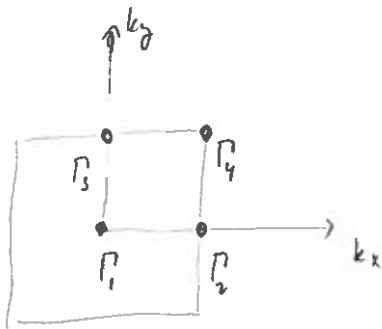
LECTURE 13

\mathbb{Z}_2 invariant recap:

- For inversion symmetric 2D insulators we showed that

$$(-1)^{\nu} = \prod_{i=1}^4 \delta_i, \quad \text{with } \delta_i = \prod_{m=1}^N \zeta_{2m} \left(\frac{\vec{k}}{i} \right)$$

↑
parity eigenvalues



$\vec{\Gamma}_i$ - TRIM (time-reversal invariant momenta)

- Often one uses adiabatic continuity to classify systems without inversion symmetry.

$$H = H_0 + H_1 \quad \rightarrow \quad H(\lambda) = H_0 + \lambda H_1$$

↑ ↑
 \mathcal{P} -symm. \mathcal{P} -breaking

- find \mathcal{P} for H_0

- study spectrum of $H(\lambda)$: if gap does not close as $\lambda: 0 \rightarrow 1$ then H is in the same phase.

• EXAMPLE : \mathbb{Z}_2 invariant for the Kane-Mele model of Graphene

$$H_{KH} = \sum_{\vec{k}} \left[\chi_0^{\alpha\beta}(\vec{k}) + \delta\chi_{KH}^{\alpha\beta}(\vec{k}) \right] c_{k\alpha}^\dagger c_{k\beta}$$

$$\chi_0(\vec{k}) = \vec{d}(\vec{k}) \cdot \vec{\sigma}$$

$$d_x(\vec{k}) = -t \sum_{p=1}^3 \cos(\vec{k} \cdot \vec{\delta}_p)$$

$$d_y(\vec{k}) = -t \sum_{p=1}^3 \sin(\vec{k} \cdot \vec{\delta}_p)$$

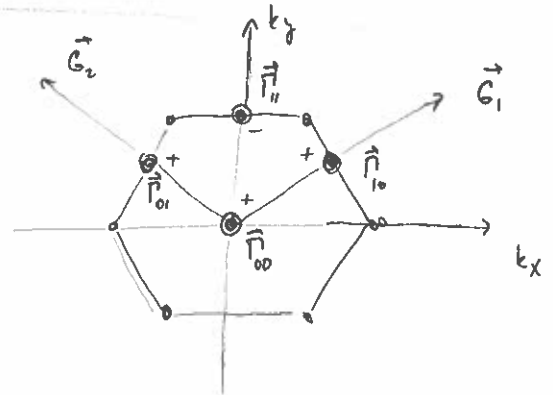
$$d_z(\vec{k}) = 0$$

$$\delta\chi_{KH}(\vec{k}) = \lambda_{so} \sigma_z s_z \sum_{p < p'=1}^3 S_{pp'} \sin \vec{k} \cdot (\vec{\delta}_p - \vec{\delta}_{p'}) \quad , \quad S_{pp'} = \pm \text{ for } p' = (p \pm 1) \text{ mod } 3$$

H_{KH} obeys both \mathcal{T} and \mathcal{P} :

$$\mathcal{T} : \quad \Theta \chi(\vec{k}) \Theta^{-1} = \chi(-\vec{k}) \quad , \quad \Theta = i s_y K$$

$$\mathcal{P} : \quad P \chi(\vec{k}) P^{-1} = \chi(-\vec{k}) \quad , \quad P = \sigma_x$$



It holds that:

$$\text{TRIM: } \vec{\Gamma}_{n_1 n_2} = \frac{1}{2} (n_1 \vec{G}_1 + n_2 \vec{G}_2) \quad , \quad n_j = 0$$

$$\chi(\vec{\Gamma}_i) = d_x(\vec{\Gamma}_i) P$$

$$[d_y(\vec{\Gamma}_i) = \delta\chi_{KH}(\vec{\Gamma}_i) = 0]$$

Since eigenvalues of $\chi(\vec{\Gamma}_i)$ for the occupied states are negative it follows that

$$\delta_i = - \text{sgn} [d_x(\vec{\Gamma}_i)]$$

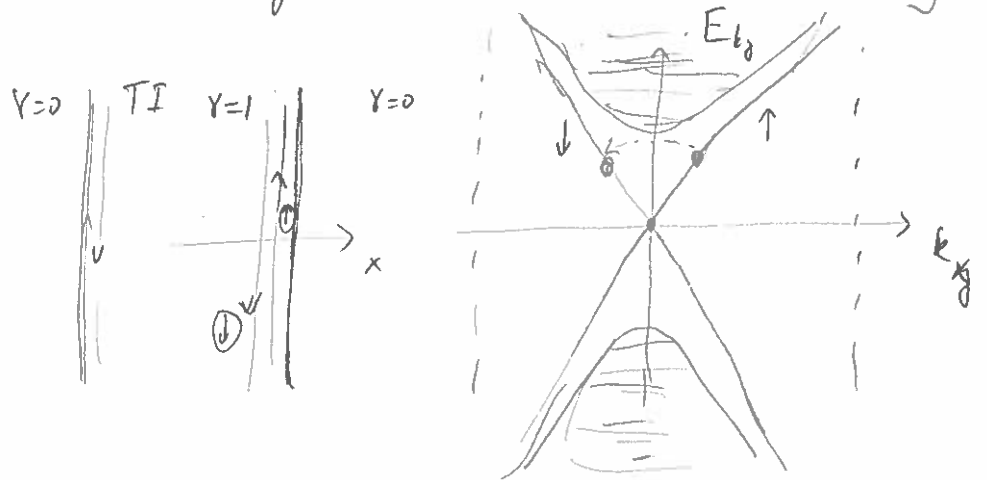
$$\left. \begin{array}{l} \delta_{00} = \delta_{01} = \delta_{10} = +1 \\ \delta_{11} = -1 \end{array} \right\} \Rightarrow \gamma = 1$$

- these terms are prohibited by symmetry, e.g. $P \delta\chi_{KH}(\vec{\Gamma}_i) P^{-1} = \delta\chi_{KH}$

H_{KH} is a
2D TI

• Properties of the edge states

[When $\nu = 1$ a pair of topologically protected, counter-propagating, spin filtered edge states exists.]



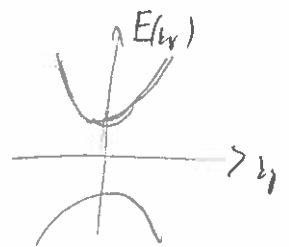
(I) The edge states are protected by \mathcal{T}

(II) Elastic backscattering is prohibited \Rightarrow edge states cannot be localized.

(I) Low-E theory

$$\mathcal{H}^{edge}(k_y) = v S_z k_y$$

$$\mathcal{T}: S_y \mathcal{H}^*(\vec{k}) S_y = \mathcal{H}(-\vec{k}) \quad \checkmark$$



To open a gap, we must add

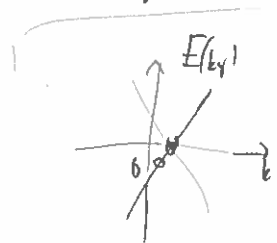
$$\delta \mathcal{H} = m_x S_x + m_y S_y,$$

$$E(k_y) = \pm \sqrt{(v k_y)^2 + m_x^2 + m_y^2}$$

but $S_y \delta \mathcal{H}^* S_y = -\delta \mathcal{H}$ \times breaks \mathcal{T} .

$$\delta \mathcal{H}' = m_z S_z$$

$$E'(k_y) = \pm |v k_y + m_z|$$

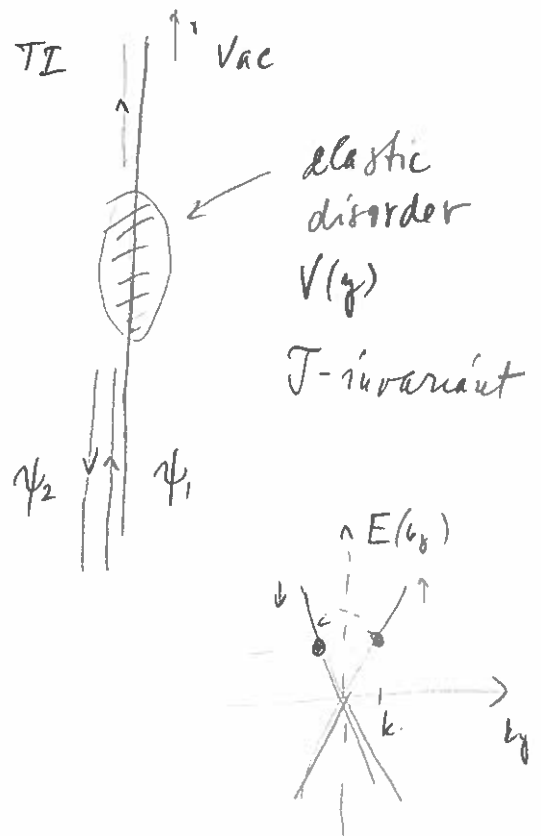


(II) Backscattering

$$\mathcal{H}^{\text{edge}} = v s_z (-i \partial_y) + V(y)$$

ψ_1 : incoming

ψ_2 : reflected



$$|\psi_2\rangle = \theta |\psi_1\rangle \quad \theta$$

$$\theta |\psi_2\rangle = -|\psi_1\rangle \quad \theta^2 = -1$$

Interested in reflection (backscattering) amplitude

$$\begin{aligned} R &= \langle \psi_1 | V | \psi_2 \rangle = \langle \psi_1 | V \theta | \psi_1 \rangle = \\ &= \langle \psi_1 | \theta V | \psi_1 \rangle \\ &= - \langle \theta \psi_2 | \theta V \psi_1 \rangle \\ &= - \langle V \psi_1 | \psi_2 \rangle \\ &= - \langle \psi_1 | V | \psi_2 \rangle = -R \end{aligned}$$

$$[V, \theta] = 0$$

$$\langle \theta a | \theta b \rangle =$$

$$\langle a | b \rangle^* = \langle b | a \rangle$$

V - hermitian

$$R = 0$$

Backscattering by T-invariant elastic disorder is prohibited.

\Rightarrow ballistic transport along the edge.

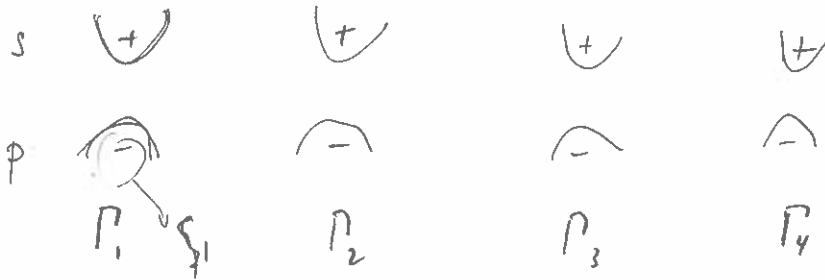
HgTe: The first experimental example of cTI.

[Th: Benning, Hughes & Zhang, Science 314 | exp: König et al, Science 318, 766 (2007)
1757/2006

HgTe is a II-VI semiconductor

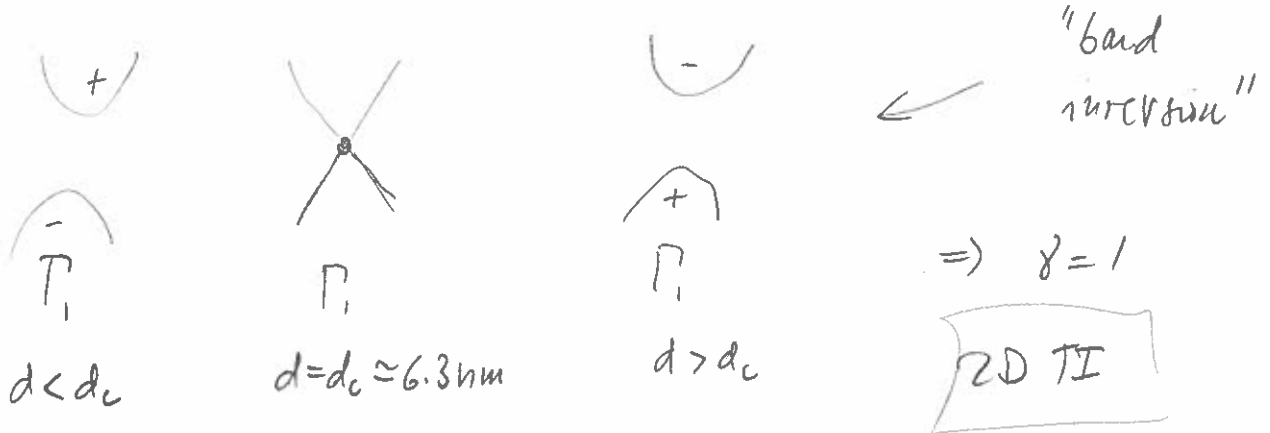
crystallizes in zincblende structure (FCC with 2-point basis)

(ZnS, CuF, MnSe) dozens different compounds



Thin film
in most
 $\gamma = 0$

HgTe strong SOC, undergoes a transition as a function of film thickness d :



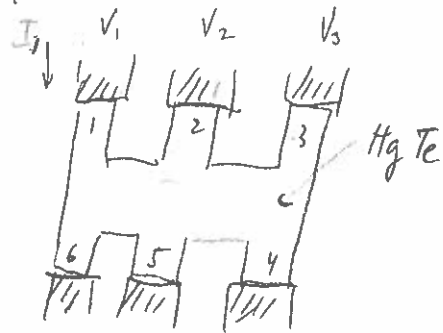
The experiment measured conductance of the edge states

expect $G = 2 \frac{e^2}{h}$ for two ballistic channels.

For a general geometry the currents can be found via the Landauer-Buttiker formula

$$I_i = \frac{e^2}{h} \sum_j (T_{ji} V_j - T_{ij} V_i)$$

$$\sum_i I_i = 0, \quad T_{ij} - \text{transmission matrix}$$



For ballistic edge states we have

$$T_{i,i+1} = T_{i+1,i} = 1, \quad \text{all others are 0}$$

$$T_{ij} = \begin{cases} 1, & i=j \pm 1 \pmod{6} \\ 0, & \text{otherwise} \end{cases} = \# \text{ of edges that connect } i \text{ and } j$$

(T_{ii} = 0)

1+1 - one for each edge

Two-terminal measurement

$$T_{12} = T_{21} = 2, \quad T_{11} = T_{22} = 0$$

$$I_1 = \frac{e^2}{h} (2V_1 - 2V_2)$$



$$= \frac{2e^2}{h} (\Delta V)$$

$$G = \frac{I}{\Delta V} = \frac{2e^2}{h} \quad \text{Conductance.}$$